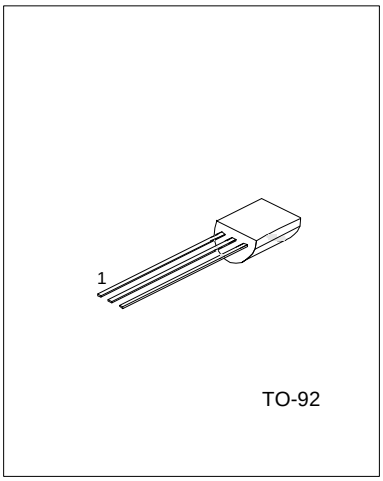
HIGH PERFORMANCE PNPN DEVICE

FEATURES

*High performance PNPN device diffused with TAG's proprietary Top Glass™ Process.
*It is Intended for general purpose applications where logic compatible gate sensitivity is required.



TO-92

1:MT1 2:G 3:MT2

ABSOLUTE MAXIMUM RATINGS (Ta=25°C ,unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Repetitive Peak Off State Voltage	V_{DRM}	Tj=-40°C to 125°C,RGK=1kΩ	600			V
On-state Current	$I_{T(RMS)}$	All conduction angles TC=50°C	0.8			A
Nonrept. On-State Current	I_{TSM}	Half Cycle,60Hz	22			A
Nonrept. On-State Current	I_{TSM}	Half Cycle,50Hz	20			A
Fusing Current	I^2t	t=10ms	2			A^2s
Peak Reverse Gate Voltage	V_{GRM}		8			V
Peak Gate Current	I_{GM}	10μs max	1.2			A
Peak Gate dissipation	P_{GM}	10μs max	3			W
Gate Dissipation	$P_{G(AV)}$	20ms max	0.2			W
Operating Temperature	Tj		-40		125	°C
Storage Temperature	Tstg		-40		150	°C
Soldering Temperature	Tsld	1.6mm from case,10s max			250	°C

ELECTRICAL CHARACTERISTICS(Ta=25°C,unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Off-State Leakage Current	I_{DRM}	VD=VDRM, RGK=1kΩ, Tj=125°C			200	μA
Off-State Leakage Current	I_{DRM}	VD=VDRM, RGK=1KΩ, Tj=25°C			5	μA
On-State Voltage	V_T	IT=1.2A,Tj=25°C			1.26	V
On-State Threshold Voltage	$V_{T(TO)}$	Tj=125°C			0.95	V
On-State Slope Resistance	rT	Tj=125°C			200	mΩ
Gate Trigger Current	IGTI+(1) IGTI-(2) IGTIII-(3) IGTIII+(4)	VD=12V			5	mA
Gate Trigger Voltage	V_{GT}	VD=12V All Quadrants			2	V

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Holding Current	IH	RGK=1kΩ			5	mA
Critical Rate of Voltage Rise	dv/dt	VD=0.67 x VDRM, RGK=1kΩ, Tj=125°C	30			V/μs
Critical Rate of Rise, Off-State	dv/dtc	IT=0.8A, di/dt=0.35A/ms, TC=50°C	1			V/μs
Gate Controlled Delay Time	tgd	IG=25mA,diG/dt=0.25A/μs			2.5	μs
Thermal resistance junc. to case	Rθjc				90	K/W
Thermal resistance junc. to amb.	Rθja				180	K/W